



DAS-NM10D16B

# **Product Feature**



High conversion efficiency ≥ 25%



Bifaciality ≥85%



High resistance of PID (Potential Induced Degradation)



"0" LID (Light Induced Degradation)



Power temperature coefficient ≤-0.30%/K



Weak light response (200W/m²) ≥97%



Lower CTM loss, better for the high efficiency module

## **Management System Certification**

ISO 9001: 2015 Quality Management System

ISO 14001: 2015 Environmental Management System

ISO 45001: Occupational Health and Safety Management System

#### **Quality Control**

Efficiency test accuracy is  $\pm 0.1\%$ 

100% automatic inspection of IV/EL/Appearance

Calibration Cell soure to Fraunhofer ISE

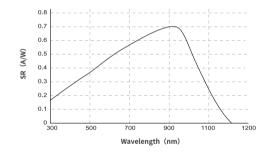
Product Features				
Dimension	182mmx182mm±0.25mm,Φ247±0.25mm			
Cell Thickness	135µm±13.5µm			
Front side	0.03±0.015mm wide bus bars, 132fingers, SiOxNy			
Back side	0.03±0.015mm wide bus bars, 134fingers, SiN			

Temperature Coefficients	
Current Temperature Coefficient	Tkcurrent: +0.045 %/K
Voltage Temperature Coefficient	Tkvoltage: -0.25 %/K
Power Temperature Coefficient	Tkpower: -0.30%/K

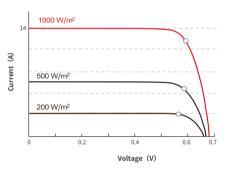
Electrical D	ata					
Eff(%)	Pmpp(W)	Umpp(V)	Impp(A)	Uoc(V)	Isc(A)	FF(%)
25.0	8.25	0.634	13.027	0.720	13.719	83.56
24.9	8.22	0.632	13.016	0.719	13.699	83.46
24.8	8.19	0.630	13.005	0.718	13.680	83.36
24.7	8.16	0.628	12.993	0.717	13.660	83.26
24.6	8.12	0.626	12.982	0.716	13.640	83.16
24.5	8.09	0.624	12.971	0.715	13.620	83.06
24.4	8.06	0.622	12.960	0.714	13.600	82.96
24.3	8.02	0.620	12.948	0.713	13.579	82.86
24.2	7.99	0.618	12.937	0.712	13.559	82.76
24.1	7.96	0.616	12.925	0.711	13.538	82.66
24.0	7.92	0.614	12.913	0.710	13.517	82.56

<sup>\*</sup>Standard Test Conditions:1000W/ m², AM 1.5, 25°C Specifications and data are only for reference.

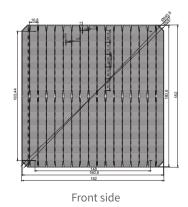
### **Spectral Response (SR)**

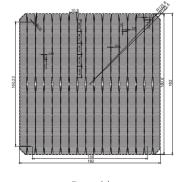


## IV Curve



### **Dimension**





Rear side



